

- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Low Gate Charge
- Lead-Free
- RoHS Compliant, Halogen-Free

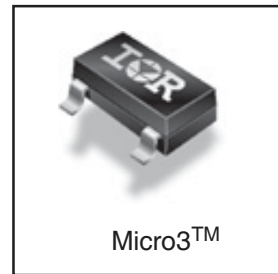
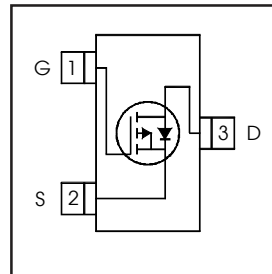
HEXFET® Power MOSFET

V_{DS}	$R_{DS(on)}$ max (m Ω)	I_D
-30V	98 @ $V_{GS} = -10V$	-3.0A
	165 @ $V_{GS} = -4.5V$	-2.6A

Description

These P-channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications.

A thermally enhanced large pad leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3™, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards. The thermal resistance and power dissipation are the best available.



Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRLML5203TRPbF	Micro3™ (SOT-23)	Tape and Reel	3000	IRLML5203TRPbF

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-30	V
I_D @ $T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-3.0	A
I_D @ $T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-2.4	
I_{DM}	Pulsed Drain Current ①	-24	
P_D @ $T_A = 25^\circ C$	Power Dissipation	1.25	W
P_D @ $T_A = 70^\circ C$	Power Dissipation	0.80	
	Linear Derating Factor	10	mW/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

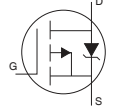
Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	100	°C/W

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

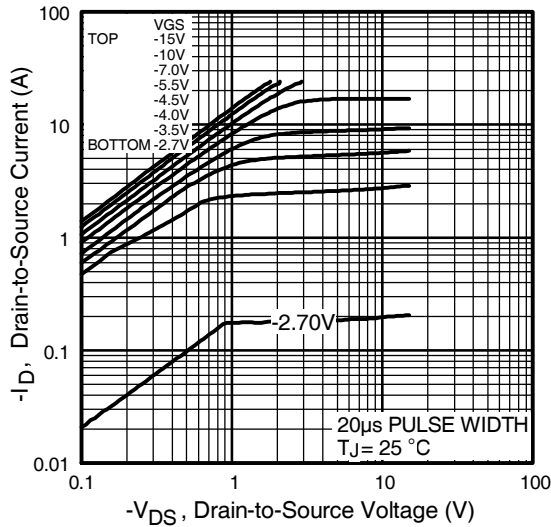
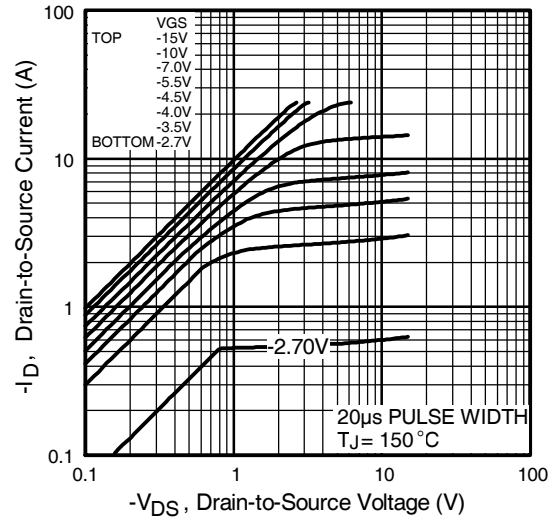
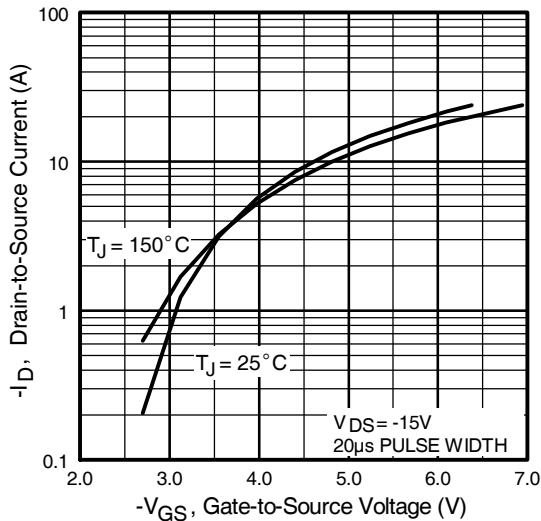
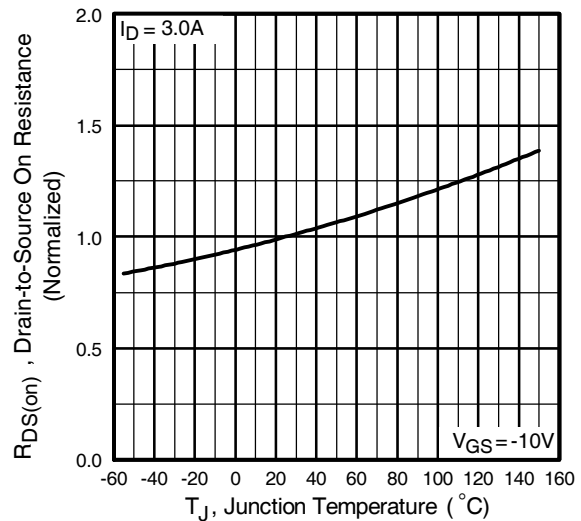
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-30	—	—	V	$V_{GS} = 0V$, $I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.019	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = -1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	98	$m\Omega$	$V_{GS} = -10V$, $I_D = -3.0A$ ②
		—	—	165		$V_{GS} = -4.5V$, $I_D = -2.6A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	-2.5	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
g_{fs}	Forward Transconductance	3.1	—	—	S	$V_{DS} = -10V$, $I_D = -3.0A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -24V$, $V_{GS} = 0V$
		—	—	-5.0		$V_{DS} = -24V$, $V_{GS} = 0V$, $T_J = 70^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
Q_g	Total Gate Charge	—	9.5	14	nC	$I_D = -3.0A$
Q_{gs}	Gate-to-Source Charge	—	2.3	3.5		$V_{DS} = -24V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	1.6	2.4		$V_{GS} = -10V$ ②
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD} = -15V$ ②
t_r	Rise Time	—	18	—		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	88	—		$R_G = 6.0\Omega$
t_f	Fall Time	—	52	—		$V_{GS} = -10V$
C_{iss}	Input Capacitance	—	510	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	71	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	43	—		$f = 1.0MHz$

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-24		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}$, $I_S = -1.3A$, $V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	17	26	ns	$T_J = 25^\circ\text{C}$, $I_F = -1.3A$
Q_{rr}	Reverse Recovery Charge	—	12	18	nC	$di/dt = -100A/\mu s$ ②

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ③ Surface mounted on FR-4 board, $t \leq 5sec$.


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature

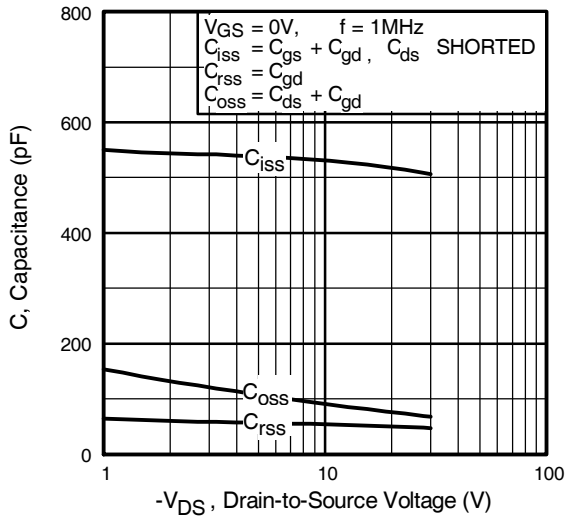


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

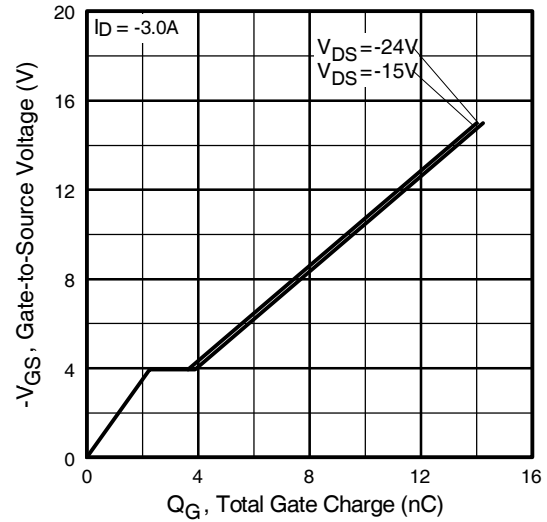


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

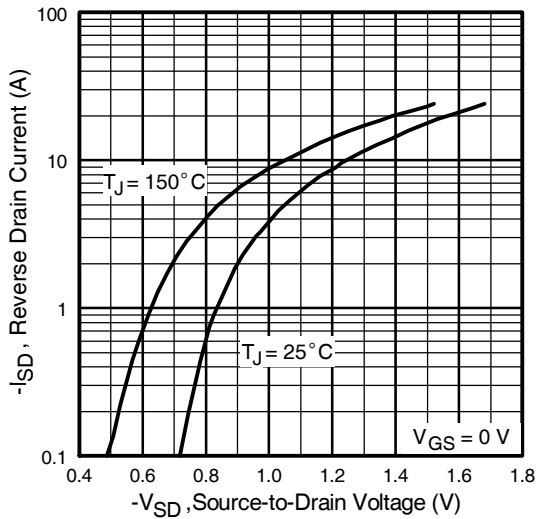


Fig 7. Typical Source-Drain Diode Forward Voltage

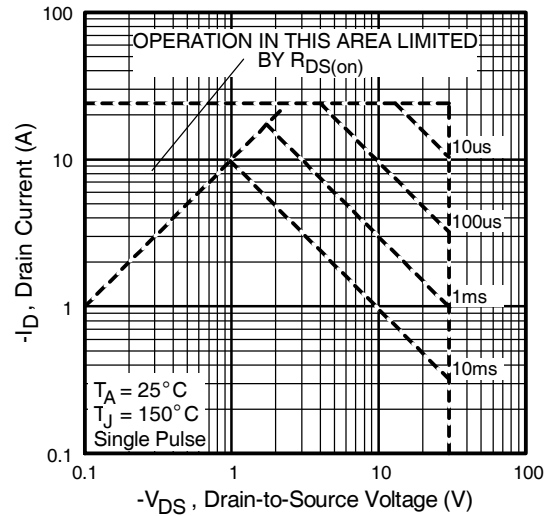


Fig 8. Maximum Safe Operating Area

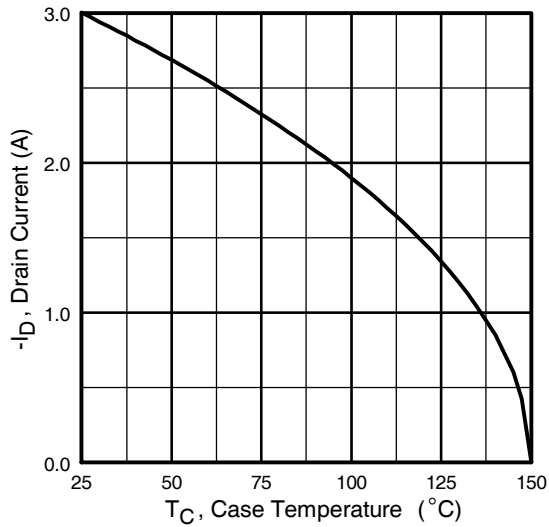


Fig 9. Maximum Drain Current Vs. Case Temperature

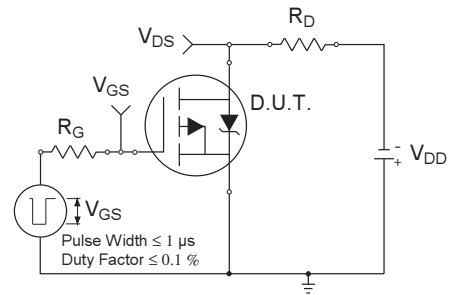


Fig 10a. Switching Time Test Circuit

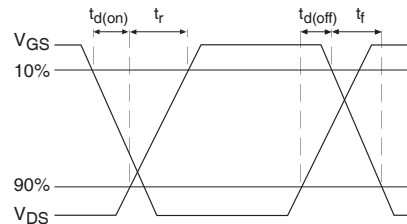


Fig 10b. Switching Time Waveforms

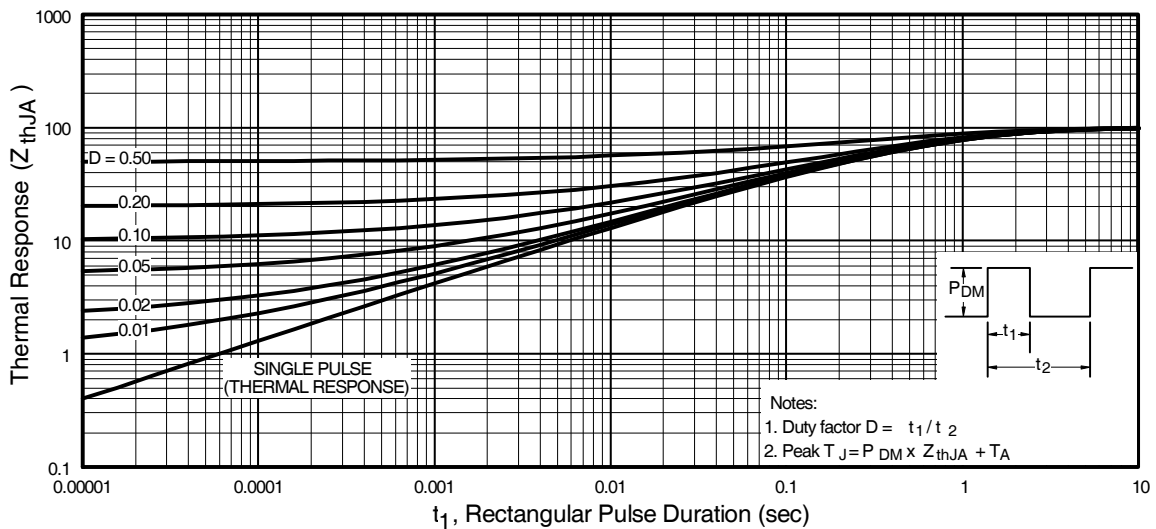


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

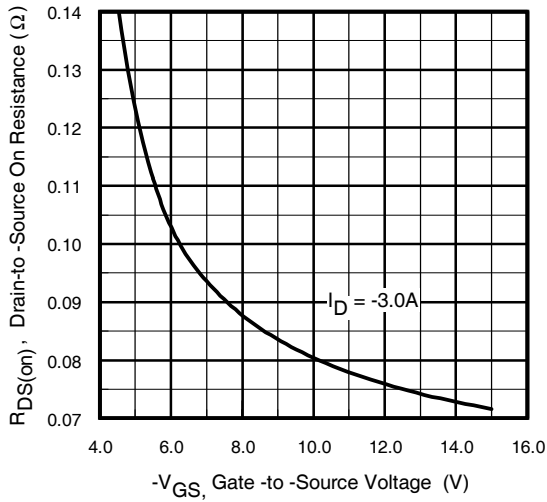


Fig 11. Typical On-Resistance Vs. Gate Voltage

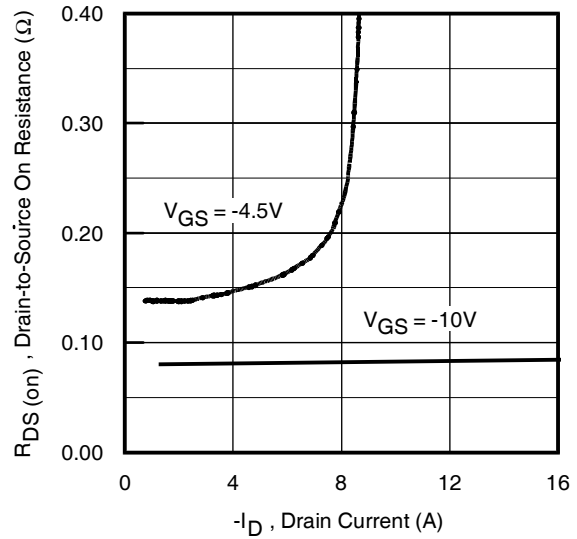


Fig 12. Typical On-Resistance Vs. Drain Current

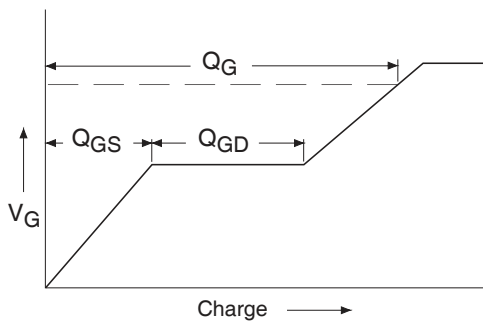


Fig 13a. Basic Gate Charge Waveform

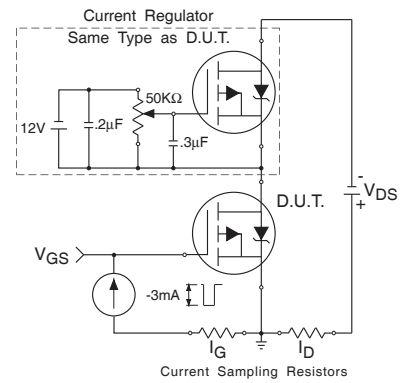


Fig 13b. Gate Charge Test Circuit

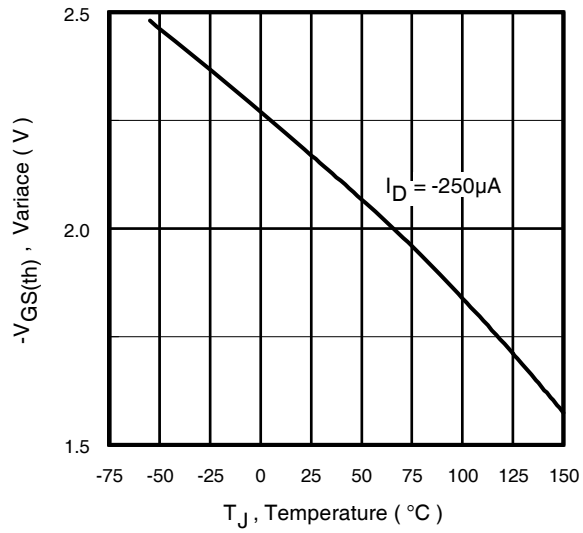


Fig 14. Threshold Voltage Vs. Temperature

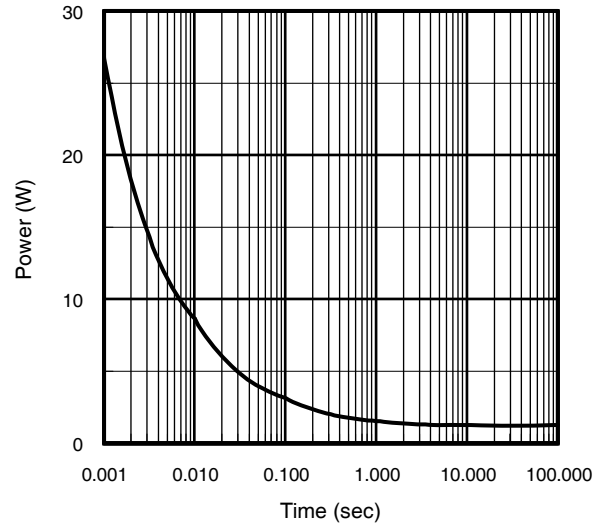


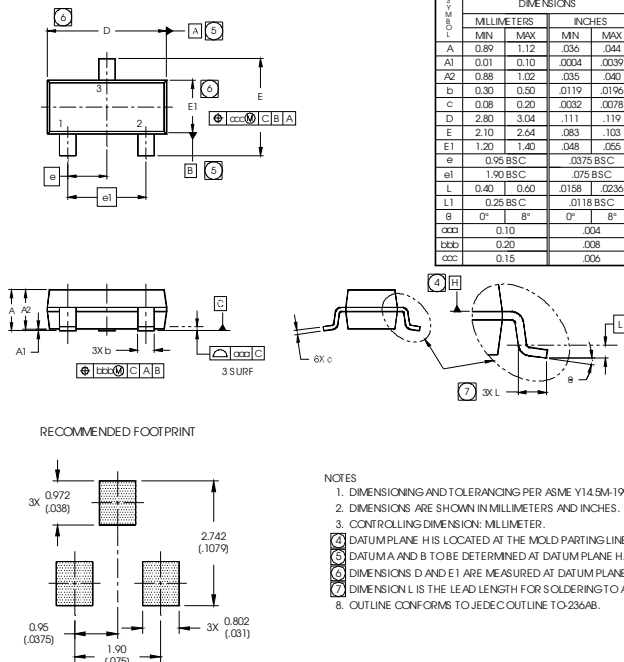
Fig 15. Typical Power Vs. Time



IRLML5203PbF

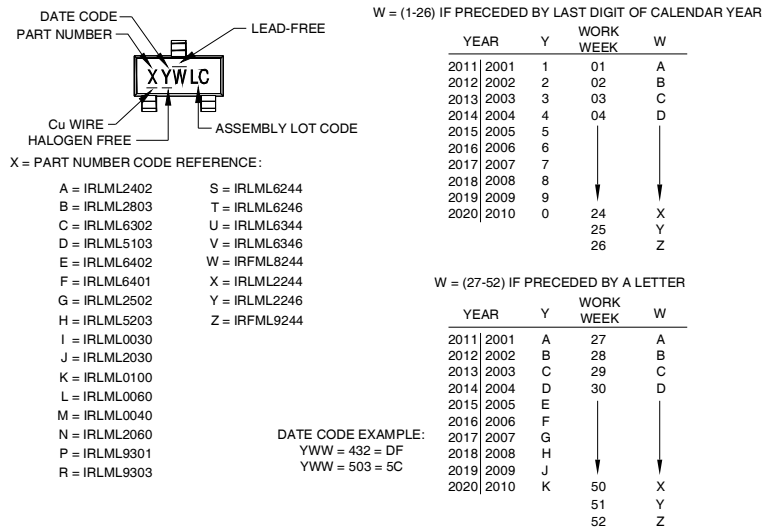
Micro3 (SOT-23) (Lead-Free) Package Outline

Dimensions are shown in millimeters (inches)



Micro3 (SOT-23 / TO-236AB) Part Marking Information

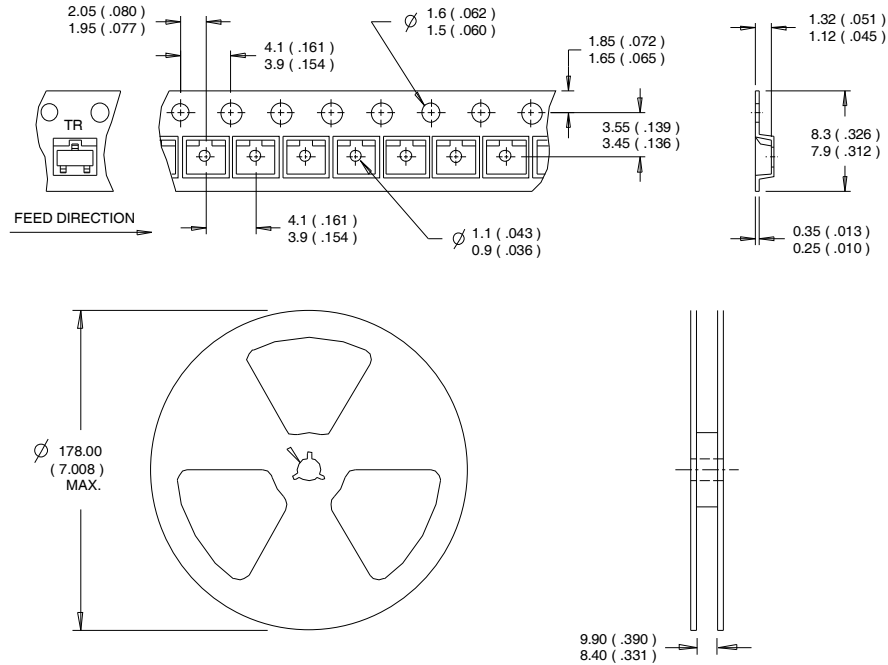
Notes: This part marking information applies to devices produced after 02/26/2001



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>

Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>

Qualification information[†]

Qualification level	Consumer (per JEDEC JESD47F ^{††} guidelines)	
Moisture Sensitivity Level	Micro3™ (SOT-23)	MSL1 (per JEDEC J-STD-020D ^{††})
RoHS compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

^{††} Applicable version of JEDEC standard at the time of product release

Revision History

Date	Comment
4/28/2014	• Updated data sheet with new IR corporate template. • Updated package outline & part marking on page 8. • Added Qualification table -Qual level "Consumer" on page 10. • Added bullet point in the Benefits "RoHS Compliant, Halogen -Free" on page 1.

International
 Rectifier

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To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>

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